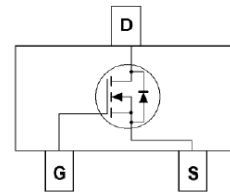


N-Channel Enhancement Mode MOSFET

Feature

- 30V/1A, $R_{DS(ON)} = 750\text{m}\Omega$ (MAX) @ $V_{GS} = 10\text{V}$, $I_{DS} = 0.60\text{A}$
 $R_{DS(ON)} = 900\text{m}\Omega$ (MAX) @ $V_{GS} = 4.5\text{V}$, $I_{DS} = 0.20\text{A}$
- Super High dense cell design for extremely low $R_{DS(ON)}$.
- Reliable and Rugged.
- SOT-23 for Surface Mount Package.



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	1	A

Electrical Characteristics $T_A=25^\circ\text{C}$ Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BVDSS	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$	30	-	-	V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=24\text{V}$, $V_{GS}=0\text{V}$	-	-	1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	$V_{GS}=20\text{V}$, $V_{DS}=0\text{V}$	-	-	100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	$V_{GS}=-20\text{V}$, $V_{DS}=0\text{V}$	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}$, $I_D=250\mu\text{A}$	1	-	-	V
Static Drain-source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=0.6\text{A}$	-	-	750	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$, $I_D=0.2\text{A}$	-	-	900	$\text{m}\Omega$
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	VSD	$V_{GS}=0\text{V}$, $I_S=0.23\text{A}$			1.2	V

单击下面可查看定价，库存，交付和生命周期等信息

[>>SHIKUES\(时科\)](#)